

# MD2009DFP

## High voltage NPN power transistor for CRT TV

### Features

- State-of-the-art technology:
  - diffused collector "enhanced generation"
- Stable performance versus operating temperature variation
- Low base drive requirement
- Tight h<sub>FE</sub> range at operating collector current
- Fully isolated power package UL compliant
- Integrated free wheeling diode

### Application

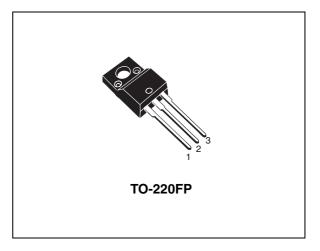
Horizontal deflection output for CRT TV

### Description

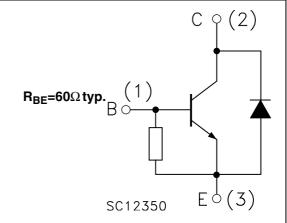
The MD2009DFP is manufactured using diffused collector in planar technology adopting new and enhanced high voltage structure. The new MD product series show improved silicon efficiency bringing updated performance to the horizontal deflection stage.

#### Table 1. Device summary

Order code	Marking	Package	Packaging
MD2009DFP	MD2009DFP	TO-220FP	Tube



#### Figure 1. Internal schematic diagram



# 1 Electrical ratings

<b>-</b>		
Table 2.	Absolute maximum rating	IS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage (V <sub>BE</sub> = 0)	1500	V
$V_{CEO}$	Collector-emitter voltage (I <sub>B</sub> = 0)	700	V
$V_{\text{EBO}}$	Base-emitter voltage (I <sub>C</sub> = 0)	7	V
Ι <sub>C</sub>	Collector current	10	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms) 16		А
Ι <sub>Β</sub>	Base current 6		А
P <sub>TOT</sub>	Total dissipation at $T_c = 25^{\circ}C$	40	W
V <sub>ISO</sub>	Isolation withstand voltage (RMS) from all three 2500		v
T <sub>stg</sub>	Storage temperature	-65 to 150 150	
Τ <sub>J</sub>	Max. operating junction temperature		

#### Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	3.12	°C/W

## 2 Electrical characteristics

(T<sub>case</sub> =25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	$V_{CE} = 1500V$ $V_{CE} = 1500V$ , $T_{c} = 125^{\circ}C$			0.2 2	mA mA
I <sub>EBO</sub>	Emitter cut-off current $(I_{C} = 0)$	V <sub>EB</sub> = 5V	40		120	mA
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage $(I_{C} = 0)$	l <sub>E</sub> = 700mA	10			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{\rm C} = 5.5 {\rm A}$ , $I_{\rm B} = 1.4 {\rm A}$			2.8	v
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	$I_{\rm C} = 5.5 {\rm A}$ , $I_{\rm B} = 1.4 {\rm A}$			1.3	v
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$ \begin{array}{ll} I_{C} = 1 A, & V_{CE} = 5 V \\ I_{C} = 5.5 A, & V_{CE} = 1 V \\ I_{C} = 5.5 A  , & V_{CE} = 5 V \end{array} $	5	18 4.7	7	
V <sub>F</sub> <sup>(1)</sup>	Diode forward voltage	I <sub>F</sub> = 5.5 A			1.6	V
t <sub>s</sub>	Inductive load Storage time	$I_{C} = 5A, f_{h} = 16KHz$ $I_{B(on)} = 1.5A, V_{BE(off)} = -2.7V$		4.5	6	μs
s t <sub>f</sub>	Fall time	$L_{\text{BB}(\text{off})} = 6.2 \mu \text{H}$		4.3 0.3	0.6	μs μs

#### Table 4. Electrical characteristics

1. Pulse test: pulse duration  $\leq$ 300 µs, duty cycle  $\leq$ 2%.



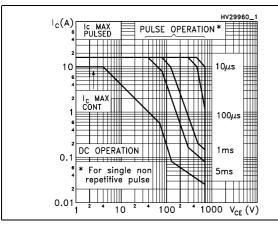
DG11570

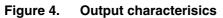
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100 125 T<sub>case</sub>(°C)

### 2.1 Electrical characteristics (curves)

#### Figure 2. Safe operating area





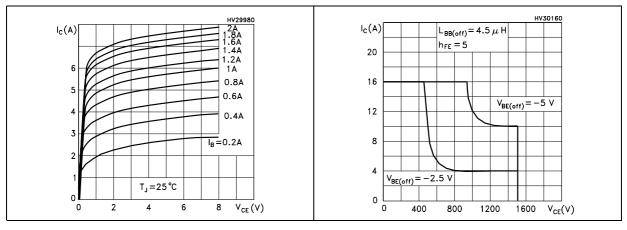


Figure 3.

P<sub>tot</sub> (%)

100

80

60

40

20

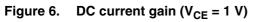
0

Figure 5.

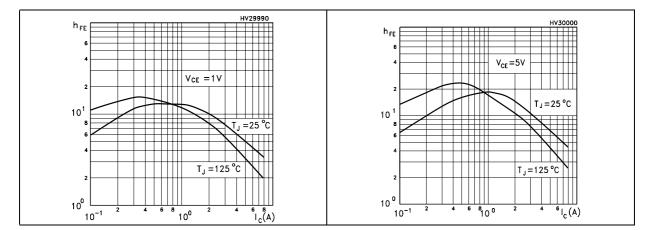
25 50 75

**Reverse biased SOA** 

**Derating curve** 









#### MD2009DFP

#### Figure 8. Collector-emitter saturation voltage Figure 9. Base-emitter saturation voltage

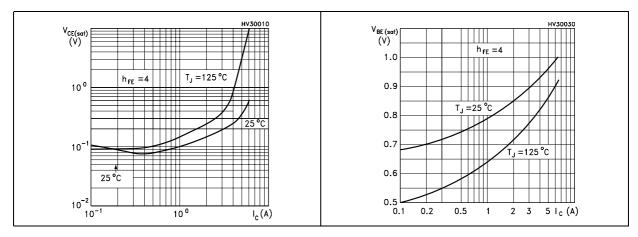
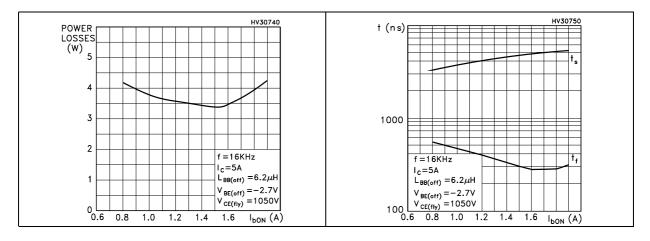


Figure 10. Power losses

Figure 11. Inductive load switching time





## 3 Test circuits

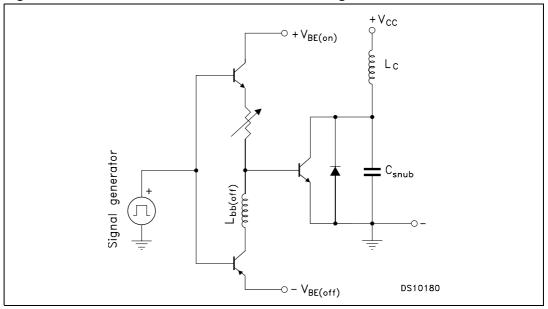
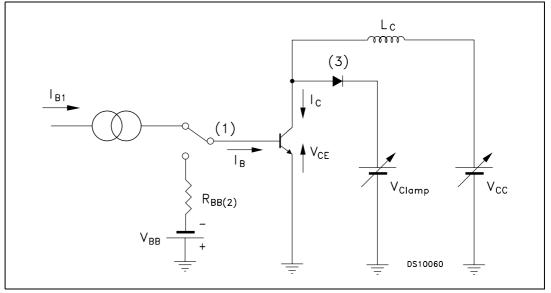


Figure 12. Power losses and inductive load switching test circuit





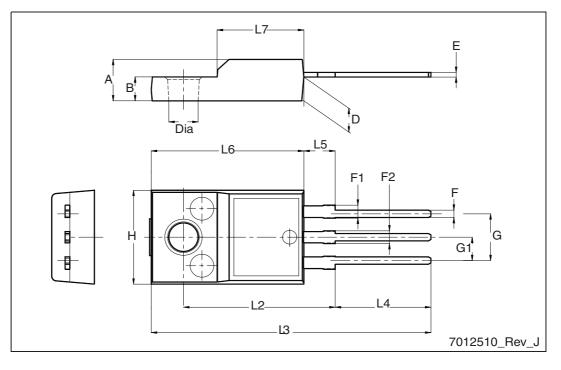


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



Dim.		mm			
	Min.	Тур.	Max.		
А	4.4		4.6		
В	2.5		2.7		
D	2.5		2.75		
E	0.45		0.7		
F	0.75		1		
F1	1.15		1.70		
F2	1.15		1.5		
G	4.95		5.2		
G1	2.4		2.7		
Н	10		10.4		
L2		16			
L3	28.6		30.6		
L4	9.8		10.6		
L5	2.9		3.6		
L6	15.9		16.4		
L7	9		9.3		
Dia	3		3.2		



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## 5 Revision history

#### Table 5.Document revision history

Date	Revision	Changes
11-Aug-2009	1	First release



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